

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. FIS920030241US1		Application No. 10/689,506	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Huajie CHEN, et al..			
				Filing Date 10/20/2003		Group 2813	

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